

UTC UNISONIC TECHNOLOGIES CO., LTD

UM6K1N

Power MOSFET

SILICON N-CHANNEL MOSFET

DESCRIPTION

The UTC UM6K1N is a silicon N-channel MOSFET. it uses UTC's advanced technology to provide the customers with a minimum on state resistance, high switching speed and low gate threshold voltage.

The UTC UM6K1N is suitable for switching and interfacing applications.

FEATURES

- * $R_{DS(on)}$ < 8 Ω @ V_{GS} =4V, I_D =10mA
- $R_{DS(on)}$ < 13 Ω @ V_{GS}=2.5V, I_D=1mA
- * High switching speed
- * Low gate threshold voltage

SYMBOL



ORDERING INFORMATION

Ordening Number Package	1	2	3	4	-		Packino		
	04		-	4	5	6	Раскілд		
UM6K1NG-AL6-R SOT-363	51	G1	D2	S2	G2	D1	Tape Reel		
Note: Pin Assignment: G: Gate D: Drain S: Source									
UM6K1NG-AL6-R (1)Packing Type (2)Package Type (3)Green Package (3) G: Halog	 (1) R: Tape Reel (2) AL6: SOT-363 (3) G: Halogen Free and Lead Free 								

MARKING





■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current	Continuous	I _D	100	mA
	Pulsed (Note 1)	I _{DM}	200	mA
Power Dissipation (Note 2)	T _C =25°C	PD	150	mW
Channel Temperature		Т _{СН}	150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pw≤10µs, Duty cycle≤50%.

3. With each pin mounted on the recommended lands.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS						÷	÷.
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =10μA, V _{GS} =0V				V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =30V, V _{GS} =0V			1.0	μA
Gate-Source Leakage Current	Forward		V _{GS} =+20V, V _{DS} =0V			+1	μA
	Reverse	IGSS	V _{GS} =-20V, V _{DS} =0V			-1	μA
ON CHARACTERISTICS						-	-
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =3V, I _D =100µA	0.8		1.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =4V, I _D =10mA		5	8	Ω
			V _{GS} =2.5V, I _D =1mA		7	13	Ω
Forward Transfer Admittance		Y _{FS}	V _{DS} =3V, I _D =10mA				mS
DYNAMIC PARAMETERS							
Input Capacitance		CISS	V _{GS} =0V, V _{DS} =5V, f=1.0MHz		13		pF
Output Capacitance		Coss			9		pF
Reverse Transfer Capacitance		C _{RSS}			4		рF
SWITCHING PARAMETERS							
Turn-ON Delay Time		t _{D(ON)}			15		ns
Rise Time		t _R	V _{DD} ≈5V, V _{GS} =5V, I _D =10mA, R _{GS} =10Ω, R _L =500Ω		35		ns
Turn-OFF Delay Time		t _{D(OFF)}			80		ns
Fall-Time		t⊦			80		ns



UM6K1N

TEST CIRCUITS AND WAVEFORMS



Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



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